DISCRETE SEMICONDUCTORS



Product specification File under Discrete Semiconductors, SC01 1996 May 06



BYG90-40 series

FEATURES

- Low switching losses
- Capability of absorbing very high surge current
- Fast recovery time
- · Guard ring protected
- Plastic SMD package.

APPLICATIONS

- Low power switched-mode power supplies
- Rectifying
- Polarity protection.

DESCRIPTION

The BYG 90-40 series consists of Schottky barrier rectifier diodes, fabricated in planar technology, and encapsulated in rectangular SOD106A plastic SMD packages.



BYG90-40 series

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode				_	1
V _R	continuous reverse voltage				
	BYG90-20		_	20	V
	BYG90-30		-	30	V
	BYG90-40		-	40	V
V _{RRM}	repetitive peak reverse voltage				
	BYG90-20		_	20	V
	BYG90-30		_	30	V
	BYG90-40		_	40	V
V _{RWM}	crest working reverse voltage				
	BYG90-20		_	20	V
	BYG90-30		-	30	V
	BYG90-40		_	40	V
I _{F(AV)}	average forward current	$T_{amb} = 65 \text{ °C}; \text{ see Fig.2};$ $R_{th j-a} = 80 \text{ K/W}; \text{ note 1};$ $V_{R(equiv)} = 0.2 \text{ V}; \text{ note 2}$	-	1	A
I _{FSM}	non-repetitive peak forward current	t = 8.3 μs half sine wave; JEDEC method	-	30	A
I _{RSM}	non-repetitive peak reverse current	t _p = 100 μs	-	0.5	A
T _{stg}	storage temperature		-65	+125	°C
Tj	junction temperature		_	125	°C

Notes

- 1. Refer to SOD106A standard mounting conditions.
- 2. For Schottky barrier diodes thermal run-away has to be considered, as in some applications, the reverse power losses P_R are a significant part of the total power losses. Nomograms for determination of the reverse power losses P_R and $I_{F(AV)}$ rating will be available on request.

BYG90-40 series

ELECTRICAL CHARACTERISTICS

 $T_{amb} = 25 \ ^{\circ}C$; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per diode	Per diode					
V _F	forward voltage	see Fig.2; note 1				
		I _F = 1 A	_	_	550	mV
		I _F = 3 A	_	_	850	mV
		I _F = 1 A; Τ _j = 100 °C	_	_	450	mV
I _R	reverse current	$V_R = V_{RRMmax}$; note 1; see Fig.3	_	-	1	mA
		$V_R = V_{RRMmax}$; $T_j = 100 \text{ °C}$; note 1; see Fig.3	_	_	10	mA
C _d	diode capacitance	$V_R = 4 V$; f = 1 MHz; see Fig.4	_	-	75	pF

Note

1. Pulsed test: $t_p = 300 \ \mu s$; $\delta = 0.02$.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	80	K/W

Note

1. Refer to SOD106A standard mounting conditions.

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GRAPHICAL DATA







BYG90-40 series

PACKAGE OUTLINE



Product specification

BYG90-40 series

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
more of the limiting values of the device at these or at	accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or may cause permanent damage to the device. These are stress ratings only and operation any other conditions above those given in the Characteristics sections of the specification limiting values for extended periods may affect device reliability.
Application information	
Where explication informat	ion is given, it is advicery and does not form part of the specification

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LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.